

# Tailoring Magnetic Exchange Interactions in Ferromagnet-Intercalated MnBi<sub>2</sub>Te<sub>4</sub> Superlattices

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**The intrinsic magnetic topological insulator  $\text{MnBi}_2\text{Te}_4$  (MBT) has provided a platform for the successful realization of exotic quantum phenomena. To broaden the horizons of MBT-based material systems, we intercalate ferromagnetic MnTe layers to construct the  $[(\text{MBT})(\text{MnTe})_m]_N$  superlattices by molecular beam epitaxy. The effective incorporation of the ferromagnetic spacer mediates the anti-ferromagnetic interlayer coupling among the MBT layers through the exchange spring effect at the MBT/MnTe hetero-interfaces. Moreover, the precise control of the MnTe thickness enables the modulation of relative strengths among the constituent magnetic orders, leading to tunable magneto-resistance responses, while the superlattice periodicity serves as an additional tuning parameter to tailor the spin configurations of the synthesized multi-layers. Our results demonstrate the advantages of superlattice engineering for optimizing the magnetic interactions in MBT-family systems, and the ferromagnet-intercalated strategy opens up new avenues in magnetic topological insulator structural design and spintronic applications.**

In magnetic topological insulators (MTIs), the co-existence of broken time-reversal symmetry (TRS) and topologically non-trivial surface states gives rise to a variety of TRS-breaking physics<sup>1-6</sup>. So far, the most commonly-adopted method to obtain MTIs is the incorporation of transition-metal elements (Cr, V, Mn) into the host TI matrix to establish the robust ferromagnetism<sup>2,7,8</sup>. However, the random distribution of magnetic atoms inevitably leads to a spatial fluctuation of the magnetic exchange gap, which restricts MTI-related phenomena at deep cryogenic temperatures<sup>9</sup>. One feasible solution to address such challenge is the design of the TI-based magnetic heterostructures in which uniform magnetic order can be induced via the interfacial proximity effect<sup>10,11</sup>. In this way, the separation of the topology and the magnetism into different layers allows us to control their contributions independently. However, due to critical lattice-matching requirements, the selection of TI-compatible magnetic films is limited and only a few MTI heterostructures have been fabricated<sup>11-13</sup>.

Alternatively,  $\text{MnBi}_2\text{Te}_4$  (MBT), an intrinsic MTI material, has aroused extensive attention in recent

years<sup>14-16</sup>. In contrast to magnetic doping, the covalently-bonded Mn atoms strictly form a two-dimensional lattice plane within the stacked Te-Bi-Te-Mn-Te-Bi-Te septuple layers (SL)<sup>17,18</sup>. This SL structure not only preserves the large spin-orbit coupling (SOC) required for band inversion, but also provides a homogeneous magnetic ground-state with intra-layer ferromagnetism (FM) and interlayer A-type anti-ferromagnetism (AFM)<sup>17</sup>. As a result, dissipationless chiral edge conduction has been observed in thin MBT flakes above 1 K, although it requires the presence of a large external magnetic field to fully magnetize the samples<sup>14,19,20</sup>.

In this context, new breakthroughs may emerge through deliberate modifications of the MBT framework, from which spontaneous magnetization can be achieved at zero magnetic field<sup>14</sup>. For instance, recent attempts by inserting the Bi<sub>2</sub>Te<sub>3</sub> spacer in the (MBT)(Bi<sub>2</sub>Te<sub>3</sub>)<sub>n</sub> ( $n = 1-6$ )-series crystals have been made, where the interlayer AFM-type Anderson super-exchange coupling strength is reduced significantly with increasing of  $n$ <sup>21-25</sup>, and this non-magnetic intercalation strategy may cause unintended magnetic fluctuations<sup>26</sup>. Instead, the Mn<sub>2</sub>Bi<sub>2</sub>Te<sub>5</sub> system has been proposed as a superior candidate given that the additional Mn layer in the Mn-Te double spacer improves the magnetic stability of the original MBT SL. Unfortunately, during the Mn<sub>2</sub>Bi<sub>2</sub>Te<sub>5</sub> single crystal growth, the Mn atoms tend to dope into MBT rather than forming the stable Mn-Te-Mn structure<sup>17</sup>, and the experimental realization of FM-intercalated MBT proposals remains elusive<sup>27</sup>.

In this work, we utilize the molecular beam epitaxy (MBE) technique to integrate ferromagnetic MnTe and MBT into [(MBT)(MnTe)<sub>m</sub>]<sub>N</sub> superlattices, where  $m$  is the nominal MnTe layer coverage,  $N$  is the number of superlattice periods, and the thickness of the MBT is fixed as one septuple layer within each period for direct comparisons. The insertion of the MnTe spacer with perpendicular FM order excels in both tuning the AFM-to-FM strength and stabilizing the interlayer exchange coupling between MBT layers. Furthermore, through deliberate superlattice periodicity control, we also manipulate the spin texture of the entire superlattice structure with configurable magneto-resistance (MR) responses. The generic design rules of FM/MBT hybrid systems may shed light on the exploration of MTI-based physics and multi-functional device applications.

**Structural and magnetic properties of MBT and [(MBT)(MnTe)<sub>m</sub>]<sub>N</sub> samples.** We first grew MBT thin films by depositing individual MnTe and Bi<sub>2</sub>Te<sub>3</sub> layers on 2-inch Al<sub>2</sub>O<sub>3</sub>(0001) substrates in an alternating sequence, followed by a moderate post-annealing procedure to form the MBT SL structure. The absence of dangling bonds on the Al<sub>2</sub>O<sub>3</sub> surface promotes the epitaxial growth of MBT, and the sharp streaky pattern of

the *in-situ* reflection high-energy electron diffraction (RHEED) reveals the two-dimensional growth mode of the as-grown MBT films (Fig. 1a). The cross-sectional high-resolution scanning transmission electron microscopy (HR-STEM) image of the MBT sample (Fig. 1b) clearly unveils the highly ordered atomic distribution of the desired Te-Bi-Te-Mn-Te-Bi-Te sequence. In addition, the quantitative analysis of the intensity distribution in Fig. 1c confirms an elemental composition ratio of Mn: Bi: Te = 1: 2: 4 in the single-crystalline thin film, and the X-ray diffraction (XRD) pattern (Supplementary Fig. 1) exhibits a series of (00*n*) peaks without observable secondary phases, both of which agree well with the ideal stoichiometric MBT values. Additionally, through the polarized neutron reflectometry (PNR) measurements of the Te-capped MBT film, the nuclear scattering length density (SLD) profile is consistent with the bulk MBT spectrum, and the magnetic SLD diagram shows a uniform magnetization distribution across the film, with a magnitude in accordance with that expected from MBT in an in-plane magnetic field, supporting high-quality growth of the designed phase (Supplementary Fig. 2-1).

Subsequently, we performed six-point magneto-transport experiments on the 5 SL MBT sample to explore its magnetic/electrical properties. Consistent with studies of exfoliated MBT flakes<sup>14,19,28</sup>, the magneto-resistance displays a hump-like line-shape at  $T = 1.5$  K, as highlighted in Fig. 1d. In particular, the initial anti-parallel alignment of spins in adjacent MBT layers leads to the high-MR state in the low-magnetic-field region, and the abrupt increase in magnitude to a MR peak near a field of  $\pm 3.3$  T (*i.e.*, defined as the transition field  $H_t$ ) corresponds to the characteristic spin-flop feature for an *A*-type AFM system<sup>14,19,28</sup>. Upon further increasing the applied magnetic field, all magnetic moments become polarized along the *z*-direction at the saturation field of  $H_s = 7$  T, and the MBT sample falls into a low-MR state. This behavior is similar to the giant magnetoresistance (GMR) effect found in a spin-valve system (the detailed GMR model is discussed in Supplementary Fig. 3). Besides, as long as the Mn:Bi:Te element ratio is accurately tuned, the corresponding anomalous Hall resistance ( $R_{xy}$ ) (Fig. 1e) reaches its saturation value of  $R_s = 4$  k $\Omega$ , which is higher than the Bi<sub>2</sub>Te<sub>3</sub>-excess and MnTe-excess MBT counterparts (see Supplementary Fig. 4). It is noted that the hybrid-AHE-like  $R_{xy}$  slope at low magnetic fields ( $\pm 3.3$  T) may be caused by native anti-site defects and/or random stacking order in MBT, which in turn modify the local electronic structures and magnetic moments<sup>25,27,29</sup>. From the aforementioned structural and electrical characterizations, we have validated the high quality of our MBT layer as a reliable building block for the following study.

Based on our previous experience with the FM-phase MnTe film growth<sup>30</sup>, we have chosen it as the intercalated layer to create the [(MBT)(MnTe)<sub>*m*</sub>]<sub>*N*</sub> system. As illustrated in Fig. 1f, by carefully choosing the

appropriate substrate temperature window and a moderate post-annealing process (Methods), the similar 2D stoichiometric structures with a negligible lattice mismatch between the FM-phase  $\alpha$ -MnTe and MBT guarantees the epitaxial growth of the superlattice structure in which the strong perpendicular ferromagnetism (*i.e.*, Curie temperature of  $T_C \sim 150$  K) of MnTe can add robust FM interactions to the hybrid system (Supplementary Fig. 5), and the surface coverage of the MnTe spacer between adjacent MBT layers  $m$  (*i.e.*, which statistically equals to the total growth time of the MnTe layer divided by that of one MnTe unit cell) can be, in principle, utilized to tune the interlayer AFM coupling<sup>31,32</sup>. It is noteworthy that the maximum thickness of the MnTe layer in this study is limited below 1.34 nm (*i.e.*, 2 MnTe layers), which is sufficiently thin to ensure effective couplings among MBT layers in the superlattice<sup>26,33</sup>.

Given the known tendency of Mn to diffuse extensively in MBT-related systems, we further performed neutron reflectometry experiments to directly probe the depth-resolved magnetization profiles in the [(MBT)(MnTe) $_m$ ] $_N$  superlattices. Firstly, an unpolarized measurement of the nominal  $m = 1.75$  sample with  $N = 10$  superlattice repeats yields an experimental MnTe layer coverage of  $m = 1.72$ , well within the experimental uncertainty of the expected value (Supplementary Fig. 2-2). Together with the appearance of the anticipated superlattice first order Bragg reflection peak at a very high reciprocal lattice vector of  $Q \approx 2.7$  nm<sup>-1</sup>, such supplementary information certifies the realization of large-area, highly periodic [(MBT)(MnTe) $_{1.75}$ ] $_{10}$  structure by MBE (Supplementary Fig. 2-2a). Next, an additional PNR measurement was conducted at  $T = 6$  K under the applied in-plane magnetic field of 3 T. Figures 2a-b summarize the best fitting results of the non-spin-flip reflectivity and spin asymmetry signals (*i.e.*, defined as the difference between the spin-dependent reflectivities normalized by their sum) in reference to the desired [(MBT)(MnTe) $_{1.75}$ ] $_{10}$  superlattice structure. While the measurement did not reach the first order Bragg reflection due to the lower intensity of the polarized neutron beam, the oscillatory SLD depth profile in Fig. 2c is in line with the periodic superlattice formation, and its average amplitude resides within the reasonable range between the bulk MBT and MnTe values. Moreover, compared with the pure 6 SL MBT data (Supplementary Fig. S2-1c), the integrated magnetic moment of the [(MBT)(MnTe) $_{1.75}$ ] $_{10}$  sample detected by PNR manifests a net contribution to the magnetization from the incorporated MnTe layers. Assuming that the magnetic moment from each constituent layer itself does not increase progressively with the applied in-plane field, our PNR results thus indicate the resulting canted spin configuration with a non-zero in-plane magnetization of 30 emu/cc (*i.e.*, noting that this value is higher than that expected from the MnTe layer alone<sup>34</sup>) may originate from the interplay between the MBT and MnTe layers through interfacial and interlayer

exchange interactions.

**Interlayer coupling mediated by the MnTe intercalation.** In order to investigate the influence of MnTe intercalation, we have conducted the temperature-dependent MR measurements on a set of  $[(\text{MBT})(\text{MnTe})_m]_5$  samples with  $m$  varying from 0 to 1.75 in Fig. 3. When the samples are cooled to  $T = 1.5$  K (below the Néel temperature of MBT  $T_N = 25$  K<sup>16</sup>), the MR signals exhibit a strong  $m$ -dependence. As disclosed in Fig. 3a, the MR peak transition field  $H_t$  monotonically shrinks with the increase of the MnTe thickness (*i.e.*, the change of  $H_t$  compared to the pure FM-phase MnTe film ( $\Delta H_t$ ) successively reduces from 2.6 T ( $m = 0.25$ ) to 0.5 T ( $m = 1.75$ ) at  $T = 1.5$  K, as marked by the red circles in Fig. 3c), signifying the effective modulation of the exchange-spring effect through the MnTe intercalation. Meanwhile, the dramatic decrease of the MR amplitude from  $m = 0$  (12.5%) to  $m = 0.5$  (2.65%) implies the suppression of the AFM-related GMR component by the introduced FM order. By further increasing  $m$ , the contribution of the MnTe layer becomes more pronounced, therefore triggering the appearance of a double-split butterfly MR response from its original curve. Eventually, the overall MR profiles of the MnTe-dominated superlattice system ( $m \geq 0.75$ ) resembles that of the pure MnTe control sample except for a larger transition field ( $H_t$ ). In fact, similar exchange-spring magnet-like MR behaviors are also observed in conventional magnetic multilayers (e.g., NiFe/IrMn and NiFe/Co stacks)<sup>32,35</sup>. Depending on the relative strengths of the anisotropy and exchange coupling energy between the magnetic components, the ground-state spin-texture of the system and its correlated magneto-transport responses can be tuned<sup>31,36</sup>. In our MnTe-intercalated MBT superlattices, when the soft magnet MnTe couples with the magnetically hard MBT single layer, the strong anisotropy of the latter can pin the magnetic moment within the MnTe layer via the magnetic proximity coupling at the interface<sup>37-41</sup>, resulting in the enlarged transition field  $H_t$ . On the other hand, as the base temperature is elevated above the  $T_N$  of MBT, the absence of the AFM-type interlayer Anderson super-exchange coupling would drive the pure 5 SL MBT sample into a paramagnetic state, as verified by the positive, parabolic MR curve detected at 30 K (*i.e.*, the MBT curve of Fig. 3b). Afterwards, the entire magneto-transport behavior of the  $[(\text{MBT})(\text{MnTe})_m]_5$  system is only governed by the remaining MnTe-related FM order. Consequently, typical butterfly-shape MR slopes with a constant peak position are recorded, regardless of the MnTe thickness (*i.e.*, same as the pure FM-type MnTe film<sup>30</sup>). Furthermore, relevant temperature-dependent  $H_t$  slopes in Fig. 3d display a clear MBT-to-MnTe transition trait as  $m$  varies from 0.25 to 1.75, providing a guidance in evaluating the competing intra-/inter-layer magnetic couplings.

In addition to enabling the coercivity modulation, the identified exchange-spring effect is found to stabilize the interlayer coupling between adjacent MBT layers in our  $[(\text{MBT})(\text{MnTe})_m]_N$  superlattices. Unlike the  $m$ -dependent  $H_t$  phenomenon noted in the low-field region, the saturation field  $H_s$ , which characterizes the interlayer exchange coupling strength, remains constant at 7 T (*i.e.*, the same value as the non-intercalated MBT film) and shows a negligible variation with respect to  $m$  (*i.e.*, the dashed straight line in Fig. 3a). In order to understand this distinctive feature, we carried out high-field anomalous Hall resistance measurements on the same set of  $[(\text{MBT})(\text{MnTe})_m]_5$  samples at low temperatures. Strikingly, the normalized Hall resistance (*i.e.*, defined as  $R_{xy}/R_s$ ) curves at  $T = 1.5$  K (Fig. 4a) shows almost identical contours, indicating a universal transition process as the magnetic moments in the superlattice are gradually aligned by the applied field. In agreement with the MR results in Fig. 3, the saturation field  $H_s$  values extracted from the AHE data at  $T = 1.5$  K, 3 K, 5 K, and 10 K also stay independent on the MnTe spacer thickness (Fig. 4b). Likewise, the  $H_s$ - $T$  slopes also follow the same temperature-scaling trace up to 25 K (Fig. 4c), above which the interlayer AFM order disappears (*i.e.*,  $H_s = 0$ ) and the overall AHE signal reverts to that of a single-phase FM-driven  $R_{xy}$  hysteresis loop.

**Modified linear chain model.** Quantitatively, the distinct evolutions of  $H_t$  and  $H_s$  versus the MnTe thickness can be well described by a modified linear chain model<sup>42-44</sup>, in which the magnetization of each constituent MBT and MnTe layer is considered as a ‘macro spin’. As schematized in Fig. 5a, the magnetic interactions in the  $[(\text{MBT})(\text{MnTe})_m]_N$  superlattice system consist of the exchange couplings between nearest-neighbored MBT-to-MBT, MnTe-to-MnTe, and MBT-to-MnTe layers, respectively. Accordingly, the total energy  $E_N$  of the system can be expressed as a function of the applied magnetic field  $\mathbf{H}$ <sup>42-44</sup>

$$\begin{aligned}
E_N(\mathbf{m}_i^{\text{MBT}}, \mathbf{m}_i^{\text{MnTe}}, \mathbf{H}) = & \sum_{i=1}^{N-1} \left[ J_i^{\text{MBT}} \mathbf{m}_i^{\text{MBT}} \cdot \mathbf{m}_{i+1}^{\text{MBT}} + J_i^{\text{MnTe}} \mathbf{m}_i^{\text{MnTe}} \cdot \mathbf{m}_{i+1}^{\text{MnTe}} + \tilde{J}_i^{\text{MBT}} (\mathbf{m}_i^{\text{MBT}} \cdot \mathbf{m}_{i+1}^{\text{MBT}})^2 \right. \\
& \left. + \tilde{J}_i^{\text{MnTe}} (\mathbf{m}_i^{\text{MnTe}} \cdot \mathbf{m}_{i+1}^{\text{MnTe}})^2 \right] - \sum_{i=1}^N J_i^{\text{ex}} \mathbf{m}_i^{\text{MBT}} \cdot \mathbf{m}_i^{\text{MnTe}} \\
& - \sum_{i=1}^N \left[ K_i^{\text{MBT}} t_i^{\text{MBT}} (\mathbf{m}_i^{\text{MBT}} \cdot \mathbf{z})^2 + K_i^{\text{MnTe}} t_i^{\text{MnTe}} (\mathbf{m}_i^{\text{MnTe}} \cdot \mathbf{z})^2 \right] \\
& - \sum_{i=1}^N (M_i^{\text{MBT}} t_i^{\text{MBT}} \mathbf{m}_i^{\text{MBT}} + M_i^{\text{MnTe}} t_i^{\text{MnTe}} \mathbf{m}_i^{\text{MnTe}}) \cdot \mathbf{H}
\end{aligned} \tag{1}$$

where  $J_i^{\text{MBT}}$  and  $\tilde{J}_i^{\text{MBT}}$  ( $J_i^{\text{MnTe}}$  and  $\tilde{J}_i^{\text{MnTe}}$ ) are the bilinear and biquadratic interlayer exchange coupling

205 constants between adjacent MBT (MnTe) layers,  $J_i^{\text{ex}}$  denotes the MBT/MnTe interfacial magnetic interaction,  
 206  $K_i^{\text{MBT}}$  ( $K_i^{\text{MnTe}}$ ),  $t_i^{\text{MBT}}$  ( $t_i^{\text{MnTe}}$ ),  $M_i^{\text{MBT}}$  ( $M_i^{\text{MnTe}}$ ),  $\mathbf{m}_i^{\text{MBT}}$  ( $\mathbf{m}_i^{\text{MnTe}}$ ) correspond to the uniaxial anisotropy  
 207 constant, thickness, saturated magnetization, and the unit vector of magnetization direction of the  $i$ th MBT  
 208 (MnTe) layer, respectively. The third term accounts for the anisotropy energy, and the fourth term represents  
 209 the field-induced Zeeman energy from the uncompensated moments. Under the exchange-spring interaction  
 210 scenario, the intercalated MnTe acts as a soft FM mediating adjacent antiparallel-coupled MBT layers, and  
 211 the impact of the  $i^{\text{th}}$  MnTe spacer on the MBT pair ( $M_i^{\text{MBT}}$  and  $M_{i+1}^{\text{MBT}}$ ) can be expressed as the modifications  
 212 of the effective interlayer exchange coupling ( $J_{\text{eff}}^{\text{MBT}}$ ) and uniaxial anisotropy ( $K_{\text{eff}}^{\text{MBT}}$ )<sup>42</sup>. Therefore, Equation  
 213 (1) can be further expressed as the simplified formula:

$$\begin{aligned}
 214 \quad E = & J_{\text{eff}}^{\text{MBT}} [\cos(\theta_i - \theta_{i+1}) + \beta \cos^2(\theta_i - \theta_{i+1})] + K_{\text{eff}}^{\text{MBT}} t_i^{\text{MBT}} (\sin^2 \theta_i + \xi \sin^2 \theta_{i+1}) \\
 215 \quad & - H_z t_i^{\text{MBT}} (M_i^{\text{MBT}} \cos \theta_i + M_{i+1}^{\text{MBT}} \cos \theta_{i+1})
 \end{aligned} \tag{2}$$

216 where  $\theta_i$  ( $\theta_{i+1}$ ) is the angle deviation between  $M_i^{\text{MBT}}$  ( $M_{i+1}^{\text{MBT}}$ ) and the magnetic easy-axis (*i.e.*,  $z$ -direction),  
 217  $\beta$  and  $\xi$  are introduced as the scaling factors of the biquadratic coupling and different anisotropy, and  $t_i^{\text{MBT}}$   
 218 is the MBT layer thickness (see Supplementary Information Section 6 for detailed discussion). From this  
 219 modified linear chain model, it is found that the transition field  $H_t$  is affected by the  $K_{\text{eff}}^{\text{MBT}}$  value whereas the  
 220 saturation field  $H_s$  is mainly decided by the  $J_{\text{eff}}^{\text{MBT}}$  magnitude (Supplementary Fig. 6). Consequently, to re-  
 221 capture the  $m$ -dependent MR behaviors observed in Fig. 3, our simulation results suggest that on one hand,  
 222 the insertion of MnTe modulates the magnetic orientation and anisotropy of the MBT layer (*i.e.*, intra-layer  
 223 MBT coupling), and the calculated ground-state magnetic configuration of the superlattice with canted spin-  
 224 polarization (right panel of Fig. 5a) is consistent with the PNR data elucidated in Fig. 2 (*i.e.*, the reduction of  
 225 the effective anisotropy energy  $K_{\text{eff}}^{\text{MBT}}$  caused by MnTe insertion is also justified by the density functional  
 226 theory calculation as discussed in Supplementary Information S7). On the other hand, the presence of MnTe-  
 227 to-MnTe interlayer coupling and induced MnTe/MBT interfacial interaction both help to preserve the effective  
 228 interlayer MBT coupling strength (*i.e.*,  $J_{\text{eff}}^{\text{MBT}} = f(J_i^{\text{MnTe}}, J_i^{\text{MBT}}, J_i^{\text{ex}})$ ) with constant  $H_s$  and  $T_N$  via the  
 229 exchange spring effect (Supplementary Fig. 8 and Fig. 9)<sup>31,45,46</sup>. Here, we should point out that once the MnTe  
 230 spacer is replaced by a non-magnetic layer (*e.g.*,  $(\text{Bi}_{1-x}\text{Sb}_x)_2\text{Te}_3$ , BST), the FM-associated exchange  
 231 interactions are absent in the resulting  $[(\text{MBT})(\text{BST})_1]_N$  counterpart (*i.e.*, confirmed by magneto-transport and  
 232 X-ray magnetic circular dichroism data of in Supplementary Figs. 10 and Fig. 11), leaving the interlayer MBT  
 233 coupling determined exclusively by the Anderson super-exchange mechanism (*i.e.*,  $J_{\text{eff}}^{\text{MBT}} = J_i^{\text{MBT}}$ ). Guided



by the same underlying physics elaborated in the modified linear-chain model, it has been reported in the (MBT)(Bi<sub>2</sub>Te<sub>3</sub>)<sub>n</sub> system, the negative correlation between the AFM-type  $J_i^{\text{MBT}}$  and the intercalation distance would also result in a rapid suppression of  $T_N$  and reduction of  $H_s$  with increasing  $n$ <sup>20,22</sup>.

**Tuning the interlayer coupling by superlattice engineering.** Finally, we show the manipulation of the magnetic/spin configuration in the [(MBT)(MnTe)<sub>m</sub>]<sub>N</sub> system through superlattice structural engineering. In pure MBT thin films, since both the intra-layer FM and interlayer AFM strength are non-adjustable with the fixed crystalline structure, Fig. 5b shows that the overall MR profile always maintains the GMR-like line-shape with slightly enlarged  $H_t$  and  $H_s$  fields as the MBT thickness varies from the 2D (4 SL) to quasi-3D (10 SL) region (the sample thicknesses are calibrated by X-ray reflectivity (XRR) in Supplementary Fig. 12 and Table 12). The reduced GMR amplitude is possibly caused by the increased bulk conduction in thicker films<sup>14,19</sup>. On the contrary, with the insertion of the MnTe spacer, the magnetic proximity effect can re-orient the magnetic moments at the MBT/MnTe interface<sup>40,41,47</sup>. Under such circumstance, it is expected that a change in the number of superlattice repeats (*i.e.*, the number of hetero-interfaces) will introduce dimension-dependent features into the related magneto-transport results. Specifically, the emerging butterfly-type double-split MR curve in the thin [(MBT)(MnTe)<sub>1.75</sub>]<sub>4</sub> sample with  $H_t = 2.5$  T suggests the existence of a sizable FM moment that is comparable with the original AFM order in the MBT/MnTe/MBT/MnTe unit, similar to other FM/AFM multi-layer systems<sup>48-50</sup>. As the repeat number increases, the added  $J_i^{\text{ex}}$  at the hetero-interfaces would promote the exchange-spring effect, as emphasized by the enlarged  $H_t$  field in Fig. 5c. Given that the adjacent MBT coupling is mediated through the sandwiched MnTe layer, the increase of superlattice repeats will cement such long-range interactions and stabilize the new ground state. Along with the reinforced canted magnetization orientation which modifies the interfacial spin scattering, it is therefore unsurprising that a more prominent AFM-type GMR behavior is obtained in the  $N = 10$  sample<sup>10,51</sup>.

## Discussion

In conclusion, we have demonstrated that combining ferromagnets with MBT facilitates the construction of intrinsic MTIs with configurable electronic structures and magnetic properties. In the FM-intercalated MBT systems, the versatile interfacial and interlayer magnetic exchange interactions offer an effective approach to shape the overall spin texture, and the AFM-to-FM transition can be well-controlled by structural engineering.

Unlike the  $(\text{MBT})(\text{Bi}_2\text{Te}_3)_n$  compounds, the insertion of the MnTe spacer triggers the exchange spring effect which plays an indispensable role in the preservation of the global AFM coupling between adjacent MBT layers throughout the superlattice structures, and this advantage endows the system to be robust against external perturbation, which is favorable for device stability considerations. More importantly, the MR responses can also be tailored via superlattice periodicity optimization, thus providing another degree of freedom in the design of practical spintronic memory/sensor prototypes over traditional magnetic multilayers. With the further exploration of exotic topological features embedded in the host MBT matrix, the  $[(\text{MBT})(\text{MnTe})_m]_N$  may serve as an advanced platform for realizing axion insulator states and MTI-based exotic quantum phenomena.

## Methods

**Sample Fabrication and Structural Characterizations:** The  $[(\text{MBT})(\text{MnTe})_m]_N$  superlattice films were grown on the  $\text{Al}_2\text{O}_3(0001)$  substrate by MBE under a vacuum level of  $1 \times 10^{-8}$  Pa. Prior to the sample growth, the  $\text{Al}_2\text{O}_3$  substrate was pre-annealed at 570 °C in order to remove the absorbed contamination. During the MBE growth, high-purity Mn and Bi atoms were evaporated from standard Knudsen cells, while Te was evaporated by a thermal cracker cell. The epitaxial growth of one septuple  $\text{MnBi}_2\text{Te}_4$  was achieved by the alternant deposition of one monolayer of  $\text{Bi}_2\text{Te}_3$  and MnTe (*i.e.*, with the substrate temperatures of 200 °C and 370 °C, respectively), followed by a moderate post-annealing at 390 °C for 3 minutes. In order to ensure the single-crystallinity of MBT with the right Bi-Mn-Te ratio as well as the precise control of the MnTe coverage in the superlattice structures, the flux ratio of each element was quantified by the *in-situ* beam flux monitor. Meanwhile, the real-time growth condition and the as-grown surface atom configuration were monitored by the reciprocal RHEED patterns. Besides, X-ray diffraction and reflectivity were performed to verify the crystal structure and calibrate the film thickness, and atomic-resolution structural characterization was performed by aberration-corrected Hitachi HF5000 STEM/TEM under the high-angle annular dark field (HAADF) STEM mode, operated at 200 kV. Cross-section TEM specimen was prepared by FEI Scios FIB.

**Transport Measurements:** The as-grown superlattices were etched into a six-probe Hall bar geometry with a dimension of 2 mm  $\times$  1 mm. The electrodes were made by welding small pieces of indium onto the contact areas. The magneto-transport measurements of the fabricated devices were performed with the  $\text{He}^4$  refrigerators (Oxford Teslatron PT system) where several experimental variables such as temperature,

magnetic field, and lock-in frequency were adjusted during the measurements. Multiple lock-in amplifiers and Keithley source meters (with an excitation AC current  $I = 1 \mu\text{A}$ ) were connected to the samples so as to enable the precise four-point lock-in experiments.

**Neutron Reflectometry:** Unpolarized neutron reflectometry measurements and polarized neutron reflectometry measurements were performed using the PBR instrument at the NIST Center for neutron research. Incident and scattered neutrons were polarized parallel or antiparallel to the direction of the applied magnetic field. Due to the 3 T applied field, no net perpendicular magnetization is expected in the plane of the film, so that the spin-flip scattering cross-sections may be neglected. We consequently measured the non-spin-flip scattering cross-sections as a function of  $Q$ , the momentum transfer vector along the film normal direction. The data was reduced using the Reductus<sup>52</sup> software package. Further unpolarized neutron reflectometry measurements were performed using the POLREF<sup>53</sup> instrument at the ISIS Neutron and Muon Source<sup>54</sup>. The incident and scattered beams were unpolarized, and the reflectivity was measured at room-temperature, well above any magnetic transition. All reflectivity analysis was performed using the Refl1D software package<sup>55</sup>.

**First-principles calculations:** The first-principle calculations were performed within the density functional theory (DFT) using the projector augmented-wave (PAW) method<sup>56</sup> as implemented in the Vienna ab initio simulation package (VASP)<sup>57,58</sup>. The exchange-correlation functional was treated under the generalized gradient approximation (GGA)<sup>59</sup>, and the energy cutoff for the plane-wave basis was set to 420 eV for all calculations. The system geometry was optimized under full relaxation with a total energy tolerance  $10^{-5}$  eV for both the bulk MBT and the MBT(MnTe)<sub>1</sub> intercalation compounds. The spin-orbit coupling effect was self-consistently included, and the 3d-orbitals of Mn atoms was considered by the DFT+U approach<sup>60</sup> introduced by Dudarev *et al.*<sup>61</sup> with  $U_{\text{eff}} = 5$  eV for all results in this work. Besides, we used the optB86b-vdW functional proposed by Klimeš *et al.*<sup>62</sup> to describe the van der Waals interactions. Furthermore, in order to calculate different interlayer magnetic configurations, we constructed the  $1 \times 1 \times 2$  supercells for all systems. The magnetic exchange coupling parameters and single-ion anisotropy parameters of both bulk MBT and the MBT(MnTe)<sub>1</sub> were obtained using the Hamiltonian model proposed by Lado *et al.*<sup>63</sup>.

**XMCD measurements:** X-ray magnetic circular dichroism (XMCD) measurements were performed on beamline I10 (BLADE) at the Diamond Light Source (Oxfordshire, UK). X-ray absorption spectroscopy spectra were recorded at the Mn  $L_{2,3}$  edges between 630 and 670 eV using surface-sensitive total electron yield (TEY) detection mode in an UHV environment ( $\sim 10^{-10}$  mbar). The measurements were carried out in an

applied out-of-plane field of up to 7 T at various temperatures with the input x-rays under normal incidence. In addition, X-ray absorption spectroscopy spectra were recorded with right ( $\sigma^+$ ) and left ( $\sigma^-$ ) circularly polarized x-rays, and XMCD signals are obtained as their difference ( $\sigma^+ - \sigma^-$ ).

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## Author contributions

X. F. Kou, and Q. Yao conceived and supervised the study. P. Chen grew the samples, performed the characterization measurements and conducted the transport measurements. Q. Yao and P. Chen analyzed the transport and characterization data. P. Chen and Y. M. Yang conducted the macro-spin simulations. J. Q. Xu and H. J. Zhang contributed the first-principle calculations. Q. Sun, A. Li, X. D. Han and J. Zou performed microscopy characterization. A. Grutter, P. Quarterman, P. P. Balakrishnan, C. Kinane, A. Caruana, and S. Langridge, performed the neutron reflectometry measurements. Barat Achinuq, Emily Heppell and Thorsten Hesjedal performed x-ray magnetic circular dichroism measurements. P. Chen, Q. Yao, Y. M. Yang and X. F.

Kou wrote the manuscript. All authors discussed the results and commented on the manuscript.

## Competing financial interests

The authors declare no competing financial interests.

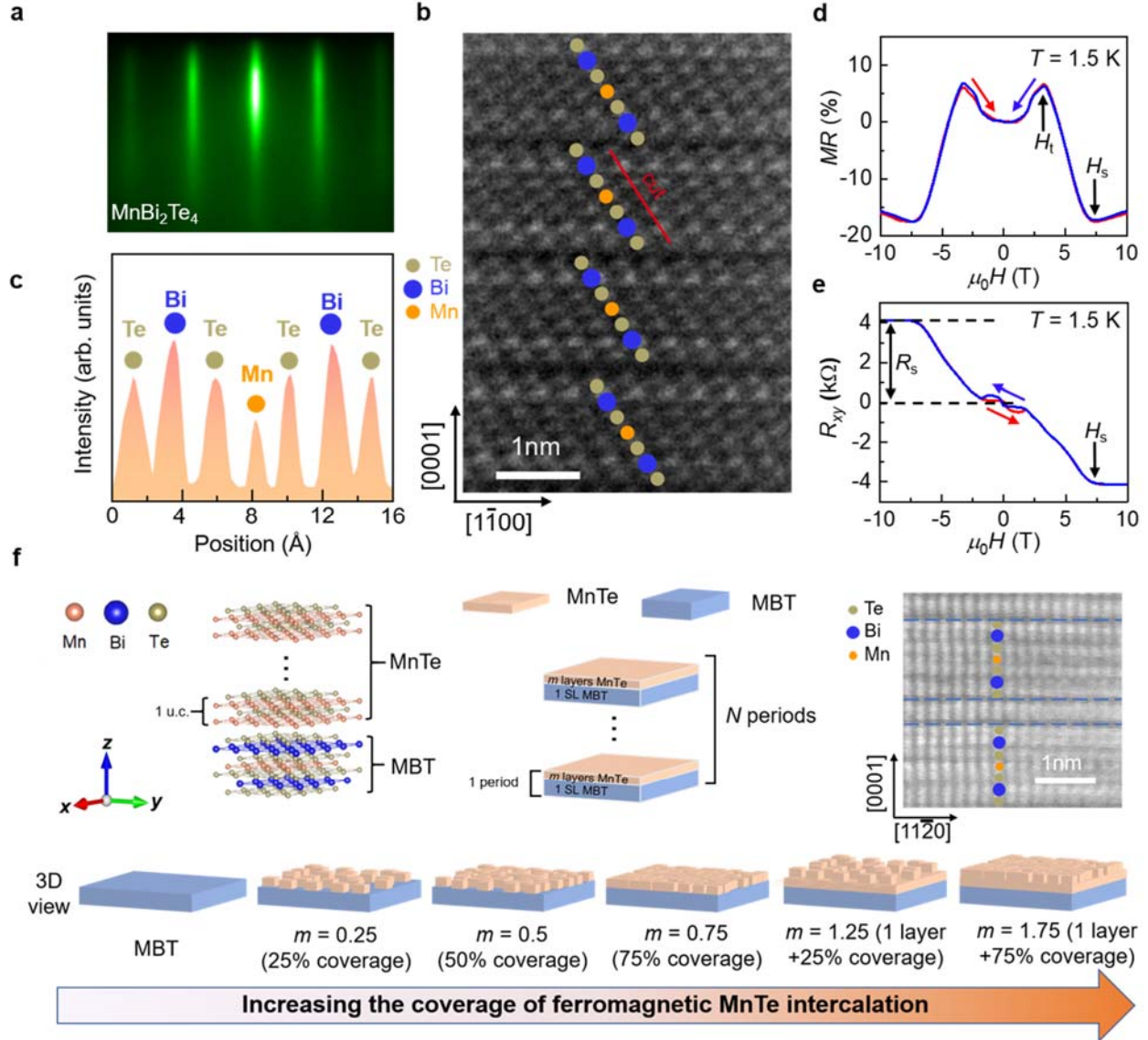
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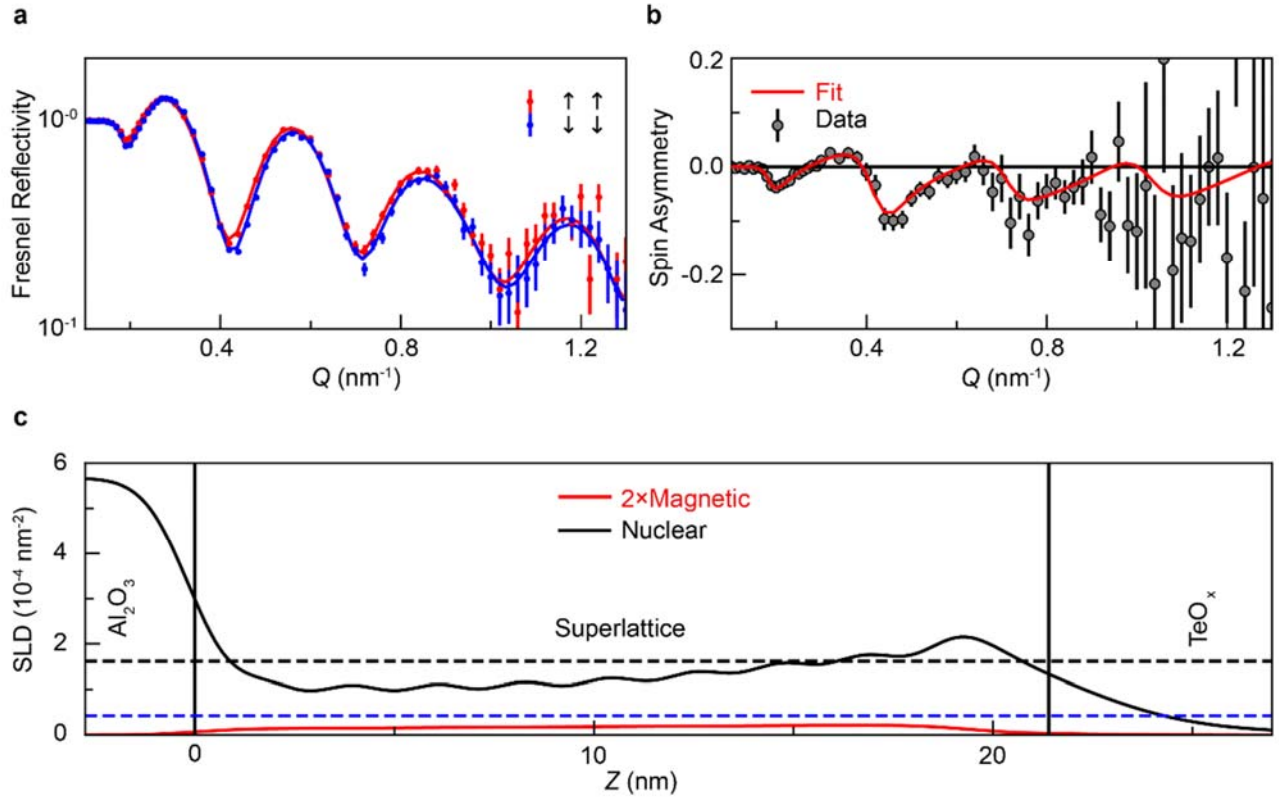
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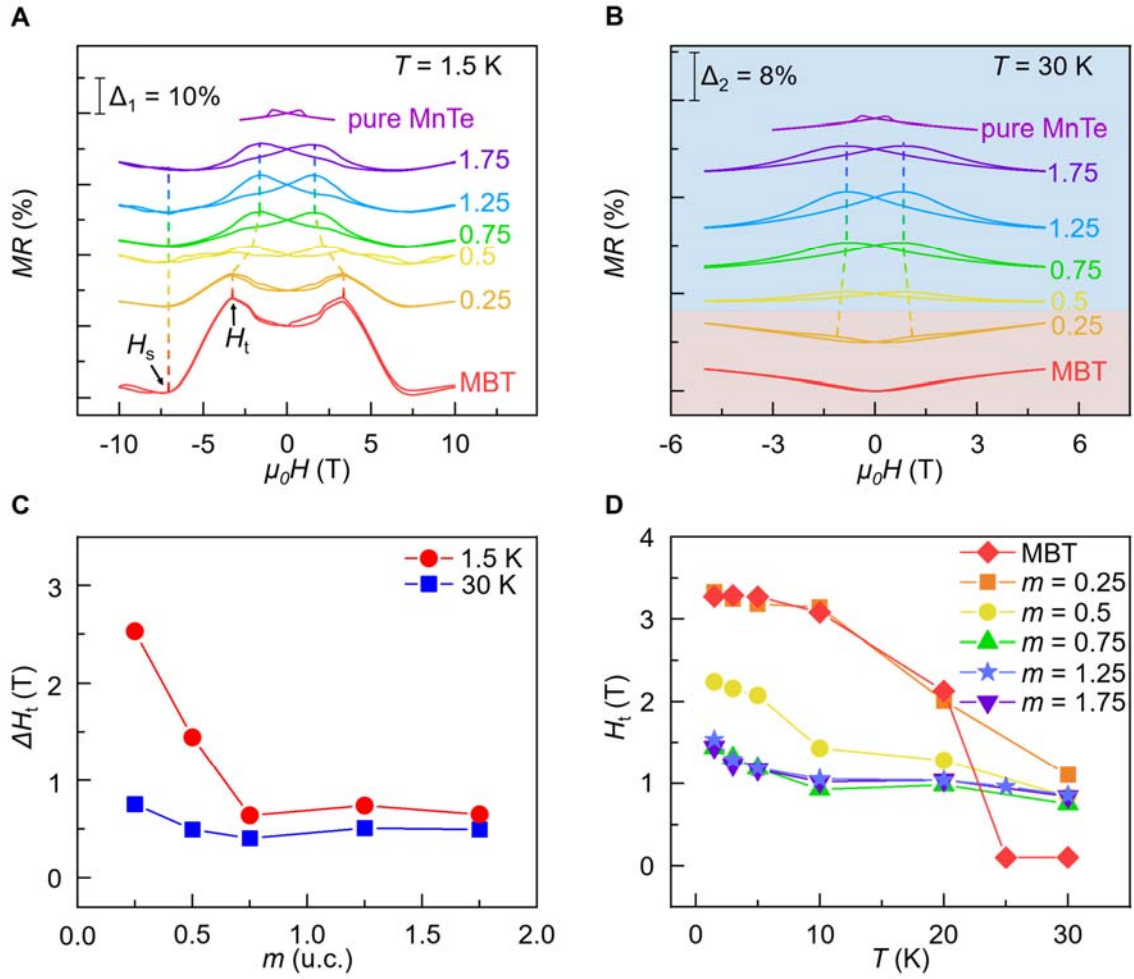


481  
 482 **Figure 1. Structural and electrical characterizations of the MBE-grown MBT thin film.** **a**, *In-situ*  
 483 RHEED with a sharp streaky pattern reveals the epitaxial growth mode. **b**, Cross-sectional HR-STEM image  
 484 of the MBT film grown on the  $\text{Al}_2\text{O}_3$  (0001) substrate. **c**, Intensity distribution mapping along the cut marked  
 485 in **b**. **d-e**, Magnetic field-dependent MR and  $R_{xy}$  data of the 5 SL MBT sample. Both the AFM-type GMR  
 486 line-shape and spin-flop-induced hysteresis loop at 1.5 K are consistent with bulk MBT data. **f**, Schematic  
 487 diagram of the FM-intercalated  $[(\text{MBT})(\text{MnTe})_m]_N$  structure and the relevant HR-STEM image. By varying  
 488 the intercalated MnTe layer coverage ( $m$ ) and superlattice repeats ( $N$ ), the magnetic exchange interactions can  
 489 be regulated.

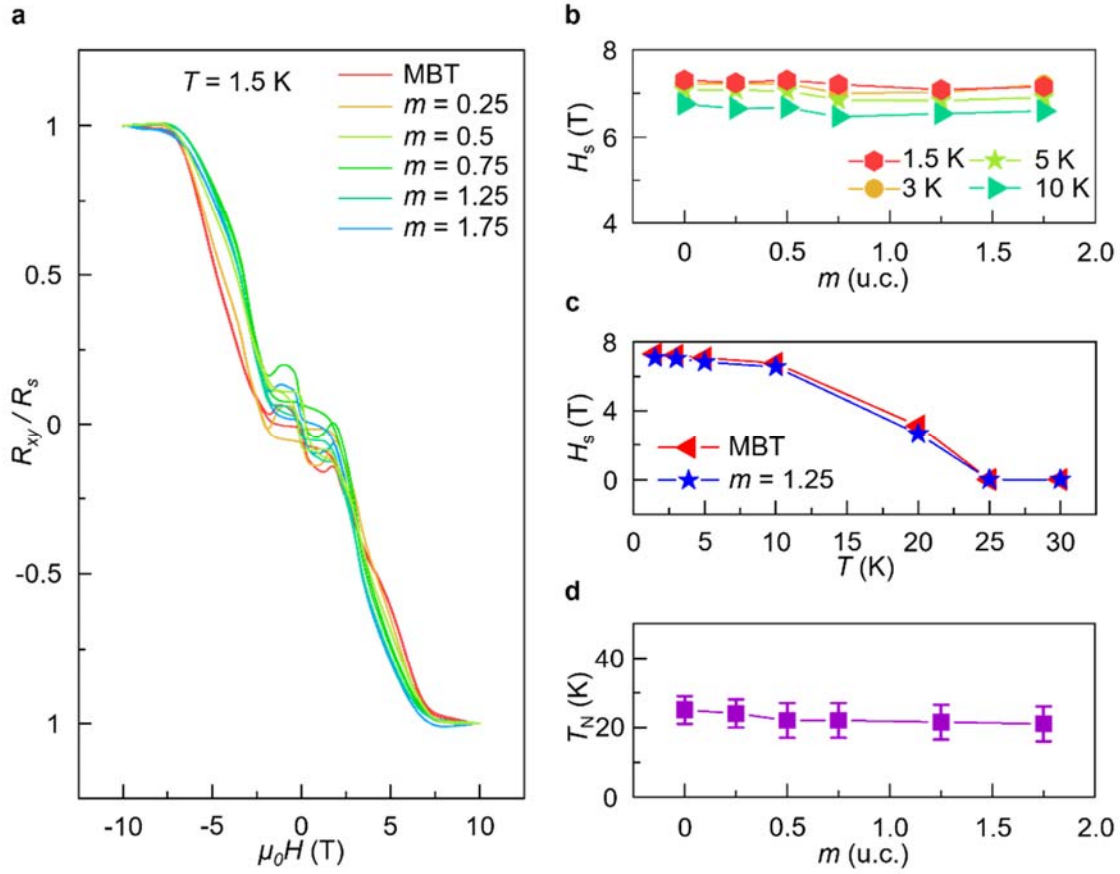




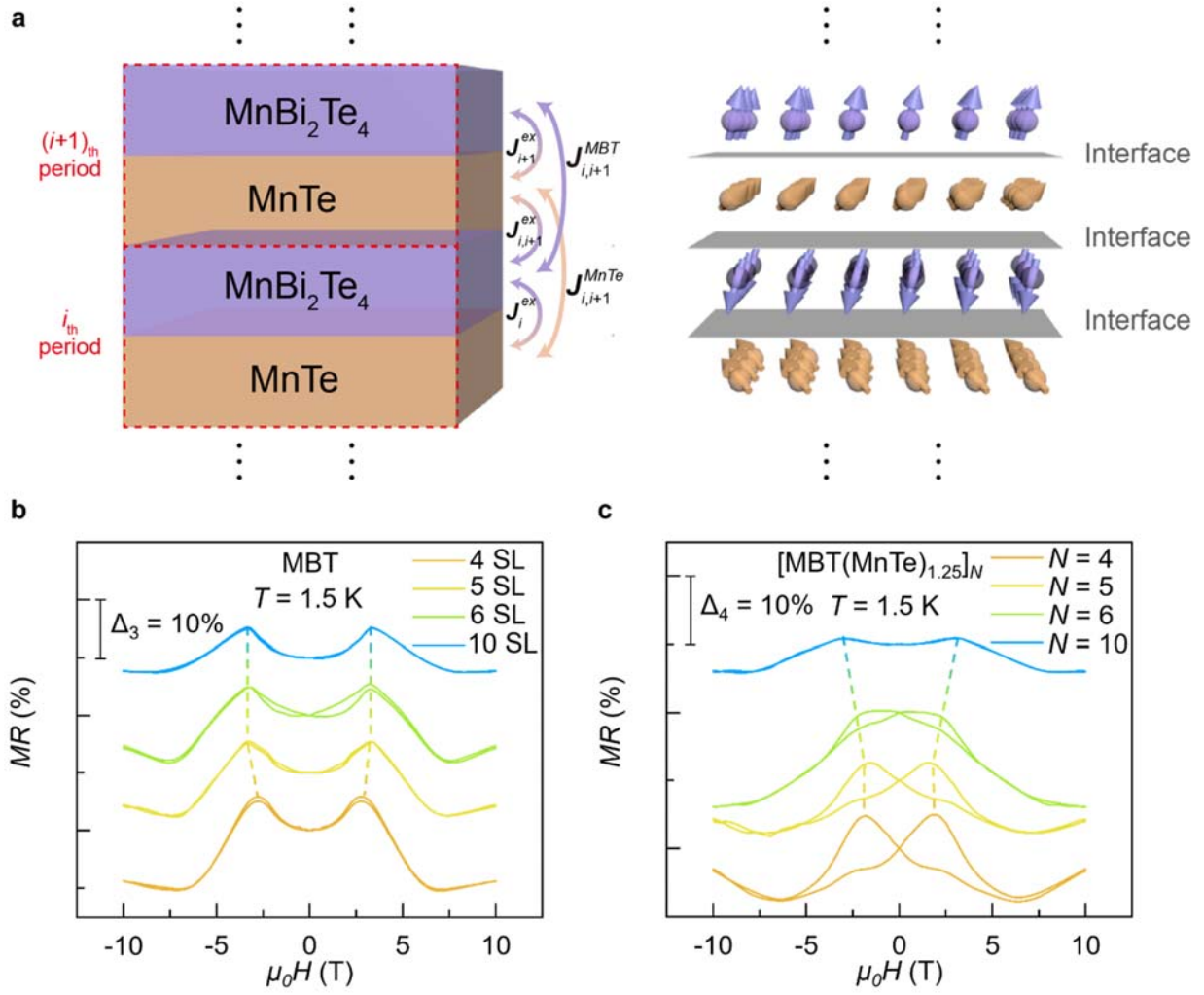
**Figure 2. Polarized neutron reflectometry measurements on the MBE-grown [(MBT)(MnTe)<sub>1.75</sub>]<sub>10</sub> superlattice.** **a-b**, Polarized neutron reflectivity and spin asymmetry alongside best fit for the Te-capped [(MBT)(MnTe)<sub>1.75</sub>]<sub>10</sub> sample. **c**, Nuclear and magnetic scattering length density (SLD) profile used to generate the fit. Error bars represent  $\pm 1$  standard deviation. Measurements were performed at  $T = 6$  K under a 3 T in-plane applied magnetic field. The black dashed line represents the expected bulk nuclear SLD of the MBT component while the blue dashed line corresponds to the ideal bulk nuclear SLD of MnTe. The depth-average magnetization of around 30 emu/cc (averaged over the whole superlattice) is obtained from the PNR data.



**Figure 3. Manipulation of the exchange spring effect in  $[(\text{MBT})(\text{MnTe})_m]_5$  samples through MnTe intercalation.** MnTe spacer thickness-dependent MR curves at **a**,  $T = 1.5$  K and **b**,  $T = 30$  K, respectively. The value of  $m$  varies from 0 to 1.75. Data are shifted vertically by  $\Delta_1$  and  $\Delta_2$  for convenient comparison. **c**, The evolutions of  $\Delta H_t$  with respect to the MnTe thickness. The negative correlation between  $\Delta H_t$  and  $m$  at  $1.5$  K (red circles) manifests the exchange spring effect whereas the constant  $\Delta H_t$  values at  $30$  K (blue squares) confirm the absence of the AFM order in the system above the Néel temperature. **d**, The temperature-dependent  $H_t$  traces of the  $[(\text{MBT})(\text{MnTe})_m]_5$  samples exhibit a clear MBT-to-MnTe transition feature at low temperatures.



**Figure 4. Mediation of interlayer couplings in the  $[(\text{MBT})(\text{MnTe})_m]_5$  system.** **a**,  $m$ -dependent anomalous Hall curves at  $T = 1.5$  K. All samples show the same spin-flop behavior regardless of the MnTe thickness. **b**, The extracted transition field  $H_s$  is insensitive to the  $m$  at different temperatures. **c**, Temperature-dependent  $H_s$  curve of the  $[(\text{MBT})(\text{MnTe})_{1.25}]_5$  superlattice as compared with the pure 5 SL MBT control sample ( $m = 0$ ). **d**, The Néel temperature  $T_N$  remains almost unchanged in all  $[(\text{MBT})(\text{MnTe})_m]_5$  samples, indicating the stabilization effect by the MnTe intercalation.



**Figure 5. Tunable magneto-resistance responses through superlattice engineering.** a, Illustrations of the interfacial and interlayer exchange interactions (left panel) and the resulting canted spin configuration (right panel) for the  $[(\text{MBT})(\text{MnTe})_m]_N$  superlattices based on the modified linear chain model simulation. The in-plane spin rotation is induced by  $J_i^{\text{ex}}$ . Evolutions of MR responses in b, thickness-dependent pure MBT thin films and c,  $[(\text{MBT})(\text{MnTe})_{1.25}]_N$  samples. With the number of superlattice repeats  $N$  increases from 4 to 10, the reinforced canted magnetization and long-range interactions drive the overall MR signal from the FM-dominated double-split butterfly shape towards the AFM-type GMR contour.